

6A silicon rectifier diodes 6A05 6A1 6A2 6A4 6A6 6A8 6A10



Specification

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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.
 Single phase, half wave, 60Hz, resistive or inductive load.
 For capacitive load, derate current by 20%

Type Number		6A05	6A1	6A2	6A4	6A6	6A8	6A10	UNITS
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current .375"(9.5mm) Lead Length @T _A = 60°C	I _{F(AV)}	6.0							A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	250							A
Maximum Instantaneous Forward Voltage @6.0A	V _F	0.95							V
Maximum DC Reverse Current @ T _A = 25°C at Rated DC Blocking Voltage @ T _A = 100°C	I _R	10 400							uA uA
Maximum Full Load Reverse Current, Full Cycle Average .375"(9.5mm) Lead Length @T _L =75°C	I _R	50							uA
Typical Junction Capacitance (Note 1)	C _J	100							pF
Typical Thermal Resistance (Note 2)	R _{θJA}	10							°C/W
Operating Temperature Range	T _J	-55 to+125							°C
Storage Temperature Range	T _{STG}	-55 to+150							°C